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View Online at https://aerobasegroup.com/nsn/5961-00-419-7549

Inclosure Material:

Metal

Overall Length:

1.253 inches

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-4

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 0.423 inches and 0.438 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

8.2 regulator voltage

Voltage Tolerance In Percent:

-5.0/+5.0

Current Rating Per Characteristic:

305.00 milliamperes all primaries horsepower metric and 1.18 amperes repetitive peak forward current

Power Rating Per Characteristic:

10.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity: 1 threaded stud and 1 tab, solder lug Specification Data: 81349-mil-prf-19500/124 government specification

Shelf Life:

N/a

- Unit Of Measure:
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Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.